

14A, 275V, 0.280 Ohm, N-Channel Power MOSFET

This N-Channel enhancement mode silicon gate power field effect transistor is an advanced power MOSFET designed, tested, and guaranteed to withstand a specified level of energy in the breakdown avalanche mode of operation. All of these power MOSFETs are designed for applications such as switching regulators, switching convertors, motor drivers, relay drivers, and drivers for high power bipolar switching transistors requiring high speed and low gate drive power. These types can be operated directly from integrated circuits.

Formerly developmental type TA17423.

Ordering Information

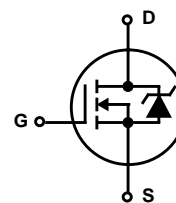
PART NUMBER	PACKAGE	BRAND
IRF646	TO-220AB	IRF646

NOTE: When ordering, use the entire part number.

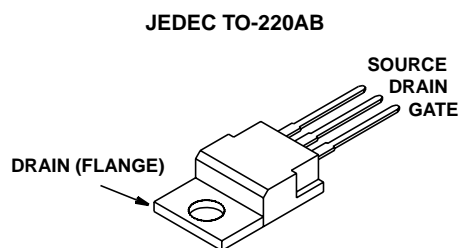
Features

- 14A, 275V
- $r_{DS(ON)} = 0.280\Omega$
- Single Pulse Avalanche Energy Rated
- SOA is Power Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance
- 275VDC Rating-120VAC Line System Operation
- Related Literature
 - TB334 "Guidelines for Soldering Surface Mount Components to PC Boards"

Symbol



Packaging



Absolute Maximum Ratings

$T_C = 25^{\circ}\text{C}$, Unless Otherwise Specified

	IRF646	UNITS
Drain to Source Voltage (Note 1)	V_{DS} 275	V
Drain to Gate Voltage ($R_{GS} = 20\text{k}\Omega$) (Note 1)	V_{DGR} 275	V
Continuous Drain Current	I_D 14	A
$T_C = 100^{\circ}\text{C}$	I_D 8.8	A
Pulsed Drain Current (Note 3)	I_{DM} 56	A
Gate to Source Voltage	V_{GS} ± 20	V
Maximum Power Dissipation	P_D 125	W
Linear Derating Factor	1.0	W/ $^{\circ}\text{C}$
Single Pulse Avalanche Energy Rating (Note 4)	E_{AS} 550	mJ
Operating and Storage Temperature	T_J, T_{STG} -55 to 150	$^{\circ}\text{C}$
Maximum Temperature for Soldering		
Leads at 0.063in (1.6mm) from Case for 10s	T_L 300	$^{\circ}\text{C}$
Package Body for 10s, See TB334.	T_{pkg} 260	$^{\circ}\text{C}$

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

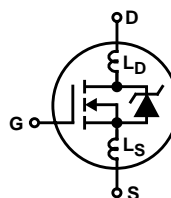
NOTE:

1. $T_J = 25^{\circ}\text{C}$ to 125°C

Electrical Specifications

$T_C = 25^{\circ}\text{C}$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Drain to Source Breakdown Voltage	BV_{DSS}	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$ (Figure 10)	275	-	-	V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$, $I_D = 250\mu\text{A}$	2	-	4	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = \text{Rated } BV_{DSS}$, $V_{GS} = 0\text{V}$	-	-	25	μA
		$V_{DS} = 0.8 \times \text{Rated } BV_{DSS}$, $V_{GS} = 0\text{V}$, $T_J = 125^{\circ}\text{C}$	-	-	250	μA
On-State Drain Current (Note 2)	$I_{D(ON)}$	$V_{DS} > I_{D(ON)} \times r_{DS(ON)MAX}$, $V_{GS} = 10\text{V}$ (Figure 7)	14	-	-	A
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20\text{V}$	-	-	± 100	nA
Drain to Source On Resistance (Note 2)	$r_{DS(ON)}$	$I_D = 8\text{A}$, $V_{GS} = 10\text{V}$ (Figures 8, 9)	-	0.200	0.280	Ω
Forward Transconductance (Note 2)	g_{fs}	$V_{DS} \geq 50\text{V}$, $I_D = 8\text{A}$ (Figure 12)	6.7	10	-	S
Turn-On Delay Time	$t_{d(ON)}$	$V_{DD} = 125\text{V}$, $I_D \approx 14\text{A}$, $R_{GS} = 9.1\Omega$, $R_L = 8.6\Omega$, MOSFET Switching Times are Essentially Independent of Operating Temperature	-	16	24	ns
Rise Time	t_r		-	67	100	ns
Turn-Off Delay Time	$t_{d(OFF)}$		-	53	80	ns
Fall Time	t_f		-	49	74	ns
Total Gate Charge (Gate to Source + Gate to Drain)	$Q_{g(TOT)}$	$V_{GS} = 10\text{V}$, $I_D = 14\text{A}$, $V_{DS} = 0.8 \times \text{Rated } BV_{DSS}$, $I_{G(REF)} = 1.5\text{mA}$, (Figure 14) Gate Charge is Essentially Independent of Operating Temperature	-	39	59	nC
Gate to Source Charge	Q_{gs}		-	6.6	-	nC
Gate to Drain "Miller" Charge	Q_{gd}		-	20	-	nC
Input Capacitance	C_{ISS}	$V_{DS} = 25\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$ (Figure 11)	-	1300	-	pF
Output Capacitance	C_{OSS}		-	320	-	pF
Reverse Transfer Capacitance	C_{RSS}		-	69	-	pF
Internal Drain Inductance	L_D	Measured from the Contact Screw on Tab to Center of Die	-	4.5	-	nH
		Measured from the Drain Lead, 6mm (0.25in) from Package to Center of Die		7.5		nH
Internal Source Inductance	L_S	Measured from the Source Lead, 6mm (0.25in) from Header to Source Bonding Pad		7.5		nH
Thermal Resistance Junction to Case	$R_{\theta JC}$		-	-	1	$^{\circ}\text{C/W}$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	Free Air Operation	-	-	80	$^{\circ}\text{C/W}$



Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Continuous Source to Drain Current	I_{SD}	Modified MOSFET Symbol Showing the Integral Reverse P-N Junction Diode	-	-	14	A
Pulse Source to Drain Current (Note 3)	I_{SDM}		-	-	56	A
Source to Drain Diode Voltage (Note 2)	V_{SD}	$T_J = 25^{\circ}\text{C}$, $I_{SD} = 14\text{A}$, $V_{GS} = 0\text{V}$ (Figure 13)	-	-	1.8	V
Reverse Recovery Time	t_{rr}	$T_J = 25^{\circ}\text{C}$, $I_{SD} = 14\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	150	300	640	ns
Reverse Recovery Charge	Q_{RR}	$T_J = 25^{\circ}\text{C}$, $I_{SD} = 14\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	1.6	3.4	7.2	μC

NOTES:

- Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
- Repetitive rating: Pulse width limited by maximum junction temperature. See Transient Thermal Impedance curve (Figure 3).
- $V_{DD} = 50\text{V}$, starting $T_J = 25^{\circ}\text{C}$, $L = 4.5\text{mH}$, $R_G = 25\Omega$, peak $I_{AS} = 14\text{A}$.

Typical Performance Curves Unless Otherwise Specified

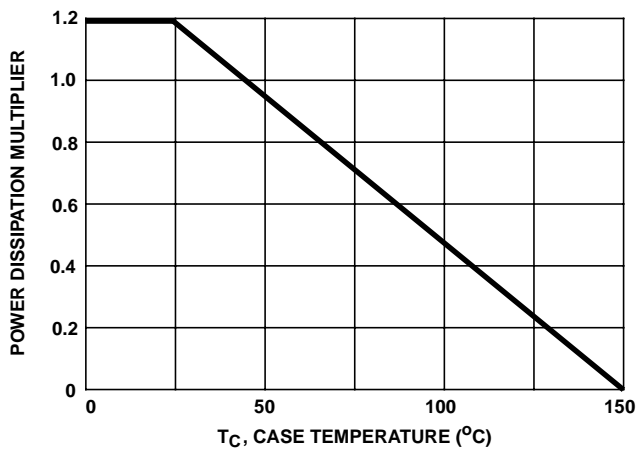


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

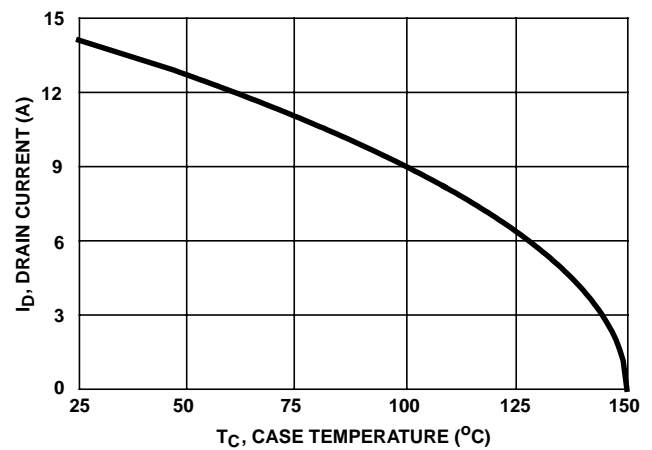


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

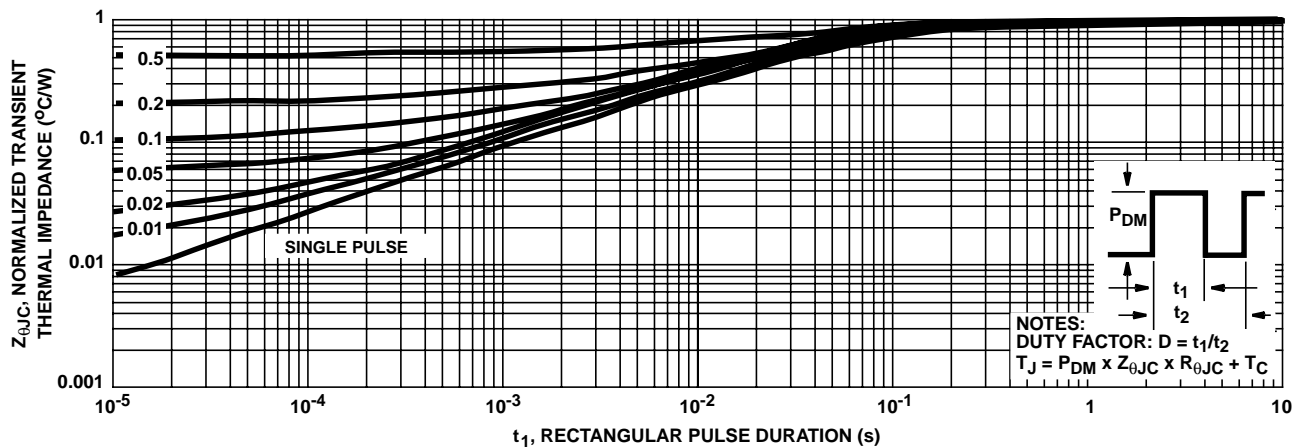


FIGURE 3. NORMALIZED MAXIMUM TRANSIENT THERMAL IMPEDANCE